

L15 ANSWER 4 OF 12 HCAPLUS COPYRIGHT 2003 ACS on STN  
 AN 2001:718959 HCAPLUS  
 DN 135:264923  
 TI Low-pressure CVD apparatus  
 IN Loan, James F.; Salerno, Jack P.  
 PA Cvd Systems, Inc., USA  
 SO U.S., 64 pp., Cont.-in-part of U.S. Ser. No. 291.871.  
 CODEN: USXXAM  
 DT Patent  
 LA English  
 IC ICM C23C014-26  
 NCL 118726000  
 CC 75-1 (Crystallography and Liquid Crystals)  
 FAN.CNT 4

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 6296711	B1	20011002	US 1999-421823	19991020
	US 2001016364	A1	20010823	US 1999-291871	19990414
	WO 2001029282	A2	20010426	WO 2000-US28998	20001020
	WO 2001029282	A3	20011122		
	US 2002076492	A1	20020620	US 2001-850454	20010507
PRAI	US 1998-60007	A2	19980414		
	US 1999-291871	A2	19990414		
	US 1999-421823	A2	19991020		
	US 1999-421828	A2	19991020		
	US 2000-678460	A2	20001003		

AB An app. for CVD includes a dispenser for dispensing a precursor to a vaporizer positioned within a vaporization chamber. A delivery conduit joins the vaporization with a process chamber. A flow meter is positioned within the delivery conduit for measuring the flow of precursor through the delivery conduit. A flow controller is likewise positioned within the delivery conduit for controlling the flow of precursor in response to the measured flow rate.  
 RL: NUU (Other use, unclassified); PEP (Physical, engineering or chemical process); PROC (Process); USES (Uses)  
 (low-pressure CVD app.)

RN 172901-22-3 HCAPLUS  
 CN Tantalum, [2-(dimethylamino-.kappa.N)ethanolato-.kappa.O]tetraethoxy-, (OC-6-23)- (9CI) (CA INDEX NAME)

